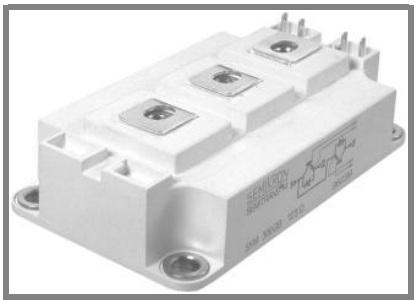
SKM 600GB126D ...



SEMITRANS® 3

Trench IGBT Module

SKM 600GB126D

SKM 600GAL126D

Preliminary Data

Features

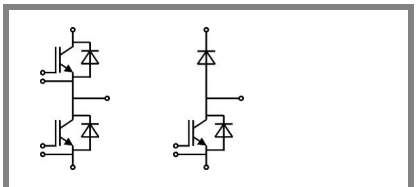
- Trench = Trenchgate technology
- V_{CEsat} with positive temperature coefficient
- High short circuit capability, self limiting to 6 x I_c

Typical Applications

- AC inverter drives
- UPS
- Electronic welders

Remarks

- $I_{DC} \leq 500A$ for $T_{Terminal} = 100$ °C



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Absolute Maximum Ratings			T_c = 25 °C, unless otherwise specified	
Symbol	**Conditions**		**Values**	**Units**
IGBT				
V_{CES}	T_j = 25 °C		1200	V
I_C	T_j = 150 °C	T_c = 25 °C	660	A
		T_c = 80 °C	460	A
I_{CRM}	I_{CRM}=2xI_{Cnom}		800	A
V_{GES}			± 20	V
t_{psc}	V_{CC} = 600 V; $V_{GE} \leq$ 20 V; V_{CES} < 1200 V	T_j = 125 °C	10	µs
Inverse Diode				
I_F	T_j = 150 °C	T_c = 25 °C	490	A
		T_c = 80 °C	340	A
I_{FRM}	I_{FRM}=2xI_{Fnom}		800	A
I_{FSM}	t_p = 10 ms; sin.	T_j = 150 °C	2880	A
Freewheeling Diode				
I_F	T_j = 150 °C	T_c = 25 °C	490	A
		T_c = 80 °C	340	A
I_{FRM}	I_{FRM}=2xI_{Fnom}		800	A
I_{FSM}	t_p = 10 ms; sin.	T_j = 150 °C	2880	A
Module				
$I_{t(RMS)}$			500	A
T_{vj}			- 40 ... + 150	°C
T_{stg}			- 40 ... + 125	°C
V_{isol}	AC, 1 min.		4000	V

Characteristics			T_c = 25 °C, unless otherwise specified			
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
IGBT						
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 16 mA		5	5,8	6,5	V
I_{CES}	V_{GE} = 0 V, V_{CE} = V_{CES}	T_j = 25 °C		0,2	0,6	mA
		T_j = 125 °C				mA
V_{CE0}		T_j = 25 °C		1	1,2	V
		T_j = 125 °C		0,9	1,1	V
r_{CE}	V_{GE} = 15 V	T_j = 25°C		1,8	2,4	mΩ
		T_j = 125°C		2,8	3,4	mΩ
$V_{CE(sat)}$	I_{Cnom} = 400 A, V_{GE} = 15 V	T_j = 25°C$_{chiplev.}$		1,7	2,15	V
		T_j = 125°C$_{chiplev.}$		2	2,45	V
C_{ies}	V_{CE} = 25, V_{GE} = 0 V	f = 1 MHz		32		nF
C_{oes}				11		nF
C_{res}				2,2		nF
Q_G	V_{GE} = -8V - +20V			3600		nC
R_{Gint}	T_j = °C			1,88		Ω
$t_{d(on)}$	R_{Gon} = 2 Ω	V_{CC} = 600V		290		ns
t_r		I_C= 400A		60		ns
E_{on}		T_j = 125 °C		39		mJ
$t_{d(off)}$	R_{Goff} = 2 Ω	V_{GE} = ± 15V		670		ns
t_f				80		ns
E_{off}				64		mJ
$R_{th(j-c)}$	per IGBT				0,055	K/W

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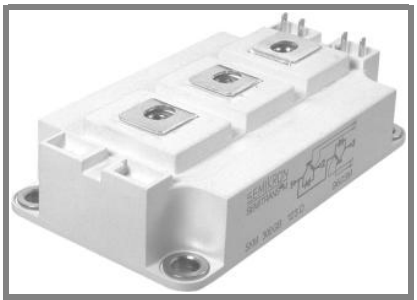


SEMITRANS® 3

Trench IGBT Module

SKM 600GB126D

SKM 600GAL126D

Preliminary Data

Features

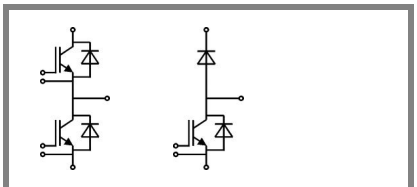
- Trench = Trenchgate technology
- V_{CEsat} with positive temperature coefficient
- High short circuit capability, self limiting to 6 x I_c

Typical Applications

- AC inverter drives
- UPS
- Electronic welders

Remarks

- $I_{DC} \leq 500A$ for $T_{Terminal} = 100$ °C



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Characteristics

Symbol	Conditions		min.	typ.	max.	Units
Inverse diode						
$V_F = V_{EC}$	I_{Fnom} = 400 A; V_{GE} = 0 V	T_j = 25 °C$_{chiplev.}$		1,6	1,8	V
		T_j = 125 °C$_{chiplev.}$		1,6	1,8	V
V_{F0}		T_j = 25 °C		1	1,1	V
		T_j = 125 °C		0,8	0,9	V
r_F		T_j = 25 °C		1,5	1,8	mΩ
		T_j = 125 °C		2	2,3	mΩ
I_{RRM}	I_F = 400 A	T_j = 125 °C		475		A
Q_{rr}	di/dt = 7600 A/µs			96		µC
E_{rr}	V_{GE} = -15 V; V_{CC} = 600 V			41		mJ
$R_{th(j-c)D}$	per diode				0,125	K/W
Freewheeling Diode						
$V_F = V_{EC}$	I_{Fnom} = 400 A; V_{GE} = 0 V	T_j = 25 °C$_{chiplev.}$		1,6	1,8	V
		T_j = 125 °C$_{chiplev.}$		1,6	1,8	V
V_{F0}		T_j = 25 °C		1	1,1	V
		T_j = 125 °C		0,8	0,9	V
r_F		T_j = 25 °C		1,5	1,8	V
		T_j = 125 °C		2	2,3	V
I_{RRM}	I_F = 400 A	T_j = 125 °C		475		A
Q_{rr}	di/dt = 7600 A/µs			96		µC
E_{rr}	V_{GE} = -15 V; V_{CC} = 600 V			41		mJ
$R_{th(j-c)FD}$	per diode				0,125	K/W
Module						
L_{CE}				15	20	nH
$R_{CC'+EE'}$	res., terminal-chip	T_{case}= 25 °C		0,35		mΩ
		T_{case}= 125 °C		0,5		mΩ
$R_{th(c-s)}$	per module				0,038	K/W
M_s	to heat sink M6		3		5	Nm
M_t	to terminals M6		2,5		5	Nm
w					325	g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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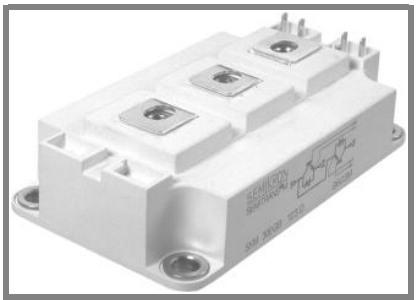

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Typical Applications

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Remarks

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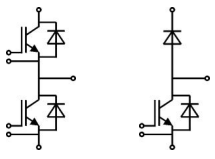
Z_{th} Symbol	Conditions	Values	Units
$Z_{th(j-c)I}$			
R_i	i = 1	38	mk/W
R_i	i = 2	13	mk/W
R_i	i = 3	3,4	mk/W
R_i	i = 4	0,6	mk/W
tau_i	i = 1	0,0836	s
tau_i	i = 2	0,009	s
tau_i	i = 3	0,0024	s
tau_i	i = 4	0,0002	s
$Z_{th(j-c)D}$			
R_i	i = 1	75	mk/W
R_i	i = 2	39	mk/W
R_i	i = 3	9,5	mk/W
R_i	i = 4	1,5	mk/W
tau_i	i = 1	0,0327	s
tau_i	i = 2	0,0101	s
tau_i	i = 3	0,002	s
tau_i	i = 4	0,0003	s



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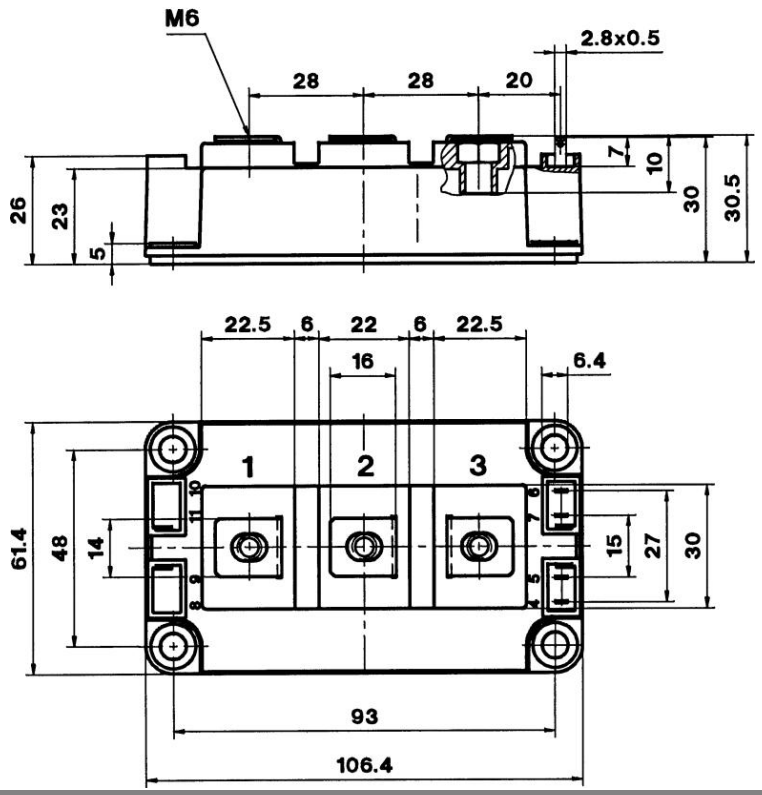

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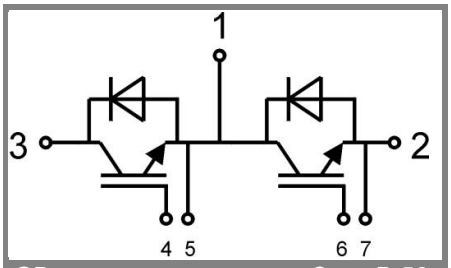

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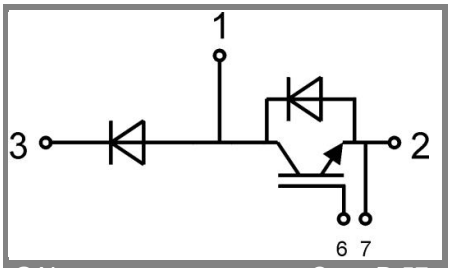

GAL Case D 57

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